

1	/20
2	/16
3	/24
4	/20
Total	/80

2 1. You have a silicon PN junction diode with $N_D=10^{19} \text{ cm}^{-3}$ and $N_A=10^{16} \text{ cm}^{-3}$

a. What is the built-in potential of the junction, V_0 ?

0.9V -1 leave as formula w/ values
 -1 leave as $\ln(\cdot) \cdot 26mV$
 -2 write formula

4 b. At room temperature, what are the n and p concentrations on each side of the unbiased junction?

$n_n = 10^{19}$	$n_p = 10^4$
$p_n = 10$	$p_p = 10^{16}$

4 c. If the temperature changes, and n_i increases by a factor of 100, what are the new carrier concentrations?

-1 both p_n, n_p off by 100

$n_n = 10^{19}$	$n_p = 10^8$
$p_n = 10^5$	$p_p = 10^{16}$

4 d. If you forward bias this diode, will the carriers in the depletion region be mostly n-type or p-type? Will the current be mostly due to drift or diffusion?

n-type, diffusion

2 e. In reverse bias, will the depletion region extend mostly into the n-type region, mostly into the p-type region, or will it be roughly equal sized in both regions?

p-type +1 if "more lightly doped side"

2 f. You have a reverse bias of 32V across the junction, and measure a capacitance of 2pF. What reverse bias should you apply to get 4pF? (accurate to 10%)

$$C_j \sim \frac{1}{\sqrt{V_R}} \quad V_R = 8$$

2 g. There is a huge charge carrier concentration gradient in an unbiased PN junction. Why don't the carriers diffuse to the other side?

OK { built-in potential
 E-field in depletion region
 fixed charges from impurity ions

2. You have a box full of identical ideal diodes. You apply 0.6V to one, and observe a current of 10mA.

4 a. What is a rough guess at the current in a single diode if you apply -0.6V across it?

-1pA

-1 missing negative sign but right answer

~~-3~~ wrong answer

-1 not knowing 60mV/decade

4 b. You wire two diodes in parallel and apply 0.6V across them. Estimate the current.

20mA

-3 not finding the answer

-1 not knowing that two parallel diodes give twice current

4 c. You wire 100 diodes in parallel and drive 10mA through them. Estimate the voltage across the pair.

0.48V

-2 not finding the answer

-2 not finding the current per each diode
($I_D = 10\text{mA}/100$)

4 d. You wire two diodes in series and apply 0.6V across the series combo. Estimate the current.

100nA

-2 not finding the current (answer)

-2 not finding the voltage $V_{BE} = 0.3\text{V}$

24' → 4' for each

2' for expressions

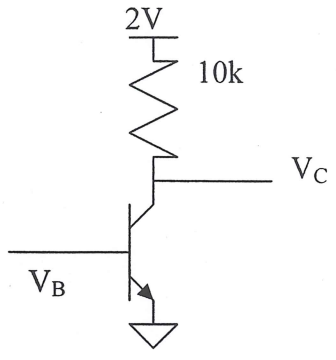
3. For the circuit below, at room temperature find the input V_B^* necessary to make $V_C^* = 1V$ and find the operating point currents I_B^* , and I_C^* . Calculate the transconductance and output resistance, and calculate the DC gain, A_V . Assume $I_S = 10^{-12} A$, $\beta = 100$, and $V_A = 100V$. Answers should be accurate to 10%.

1' for correct plug-ins
1' for final results

$V_B^* = 0.48V$ or $480mV$	$I_C^* = 100 \mu A$ or $0.1 mA$ $1 \times 10^{-4} A$	$I_B^* = 1 \mu A$ or $10^{-6} A$
$g_m = 1/260 \rightarrow$ or $1/260 S$ 4ms	$r_o = 1 M\Omega$ or $10^6 \Omega$	$A_V = -40$ or $-300/7.5$

$V_C^* = 1V$

$I_C = \frac{2V - V_C^*}{R_C} = \frac{1V}{10k} = 0.1 mA$



$I_C = I_S \cdot \exp\left(\frac{V_{BE}}{26mV}\right)$
 $1 \times 10^{-4} \quad 10^{-12}$

$V_{BE} = 8.60 mV = 0.48V$

$I_B = \frac{I_C}{\beta} = 1 \mu A$

$g_m = \left(\frac{k_B T / q}{I_C}\right)^{-1} = \left(\frac{26 mV}{0.1 mA}\right)^{-1} = (260 \Omega)^{-1} = 1/260$

$r_o = \frac{V_A}{I_C} = \frac{100V}{0.1 mA} = 1 M\Omega$

$r_{\pi} = \frac{\beta}{g_m} = \frac{10^2}{26 mV / 0.1 mA} = \frac{10^3}{26}$

$A_0 = -g_m \cdot (r_o \parallel R_C)$
 $= -g_m \cdot R_C$
 $= -260 \Omega^{-1} \cdot 10^4$
 $= -\frac{10^4}{260}$

4.

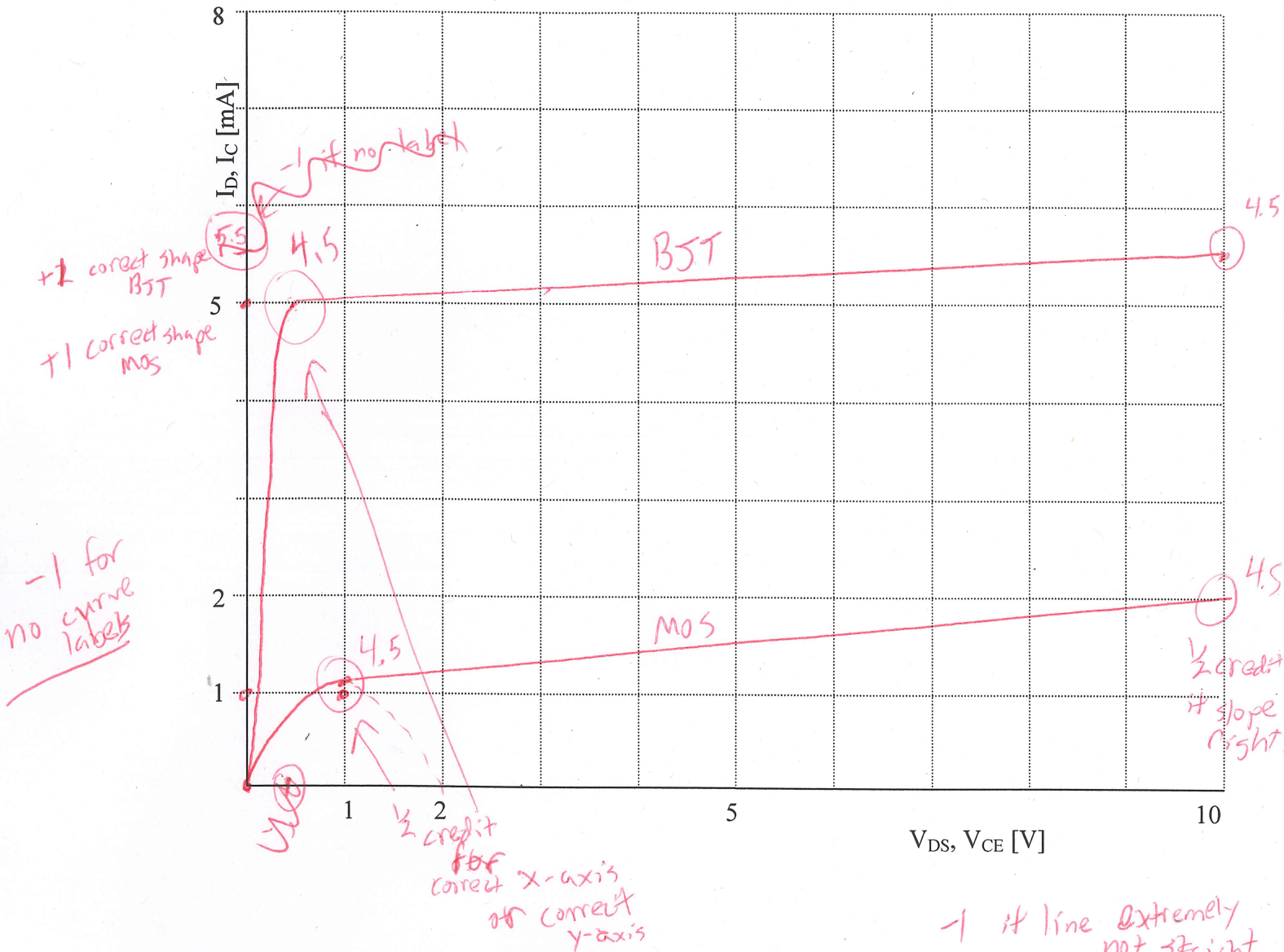
A) You have an NMOS transistor with $\mu_n C_{ox} (W/L) = 2 \text{ mA/V}^2$ and $\lambda = 0.1/\text{V}$, and $V_{TH} = 0.5 \text{ V}$. Carefully plot the drain current vs. drain voltage of the NMOS device for $V_{DS} = 0$ to 10 V and $V_{GS} = 1.5 \text{ V}$.

$$I_D = \frac{2 \text{ mA}}{2 \text{ V}^2} (V_{GS} - 0.5)^2 = 1 \text{ mA}$$

B) on the same plot, plot the collector current of an NPN bipolar transistor at room temperature with $V_A = 100 \text{ V}$, $I_S = 5 \times 10^{-13} \text{ A}$, $V_{BE} = 0.6 \text{ V}$, and $V_{CE,sat} = 0.5 \text{ V}$, for $V_{CE} = 0$ to 10 V .

$$I_C = 5 \times 10^{-3}$$

I labeled the axes for you.



Note: everyone knows roughly what these curves look like. You get points for showing me that you know *exactly* what it looks like. Be neat!

10:19 done.